



**Solid State Devices, Inc.**

14701 Firestone Blvd \* La Mirada, CA 90638  
 Phone: (562) 404-4474 \* Fax: (562) 404-1773  
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# SFF240J SFF240JR

**15 AMP, 200 Volts, 0.18  $\Omega$   
N-Channel Power MOSFET**

**DESIGNER'S DATA SHEET**

Part Number / Ordering Information <sup>1/</sup>

**SFF240J**

**Screening** <sup>2/</sup>

    — = Not Screened

    TX = TX Level

    TXV = TXV Level

    S = S Level

**Pin Configuration**

    — = Normal

    R = Reverse

**Lead Bend**

    — = Straight

    UB = Up Bend

    DB = Down Bend

- Features:**
- Rugged construction with polysilicon gate
  - Low  $R_{DS(on)}$  and high transconductance
  - Excellent high temperature stability
  - Very fast switching speed
  - Fast recovery and superior dv/dt performance
  - Increased reverse energy capability
  - Low input and transfer capacitance for easy paralleling
  - Available with Ceramic Seal. Consult Factory
  - Hermetically Sealed Isolated Power Package
  - TX, TXV, S-Level screening available
  - Replaces: IRFY240 and 2N7219 Types

Maximum Ratings	Symbol	Value	Units
Drain - Source Voltage	$V_{DS}$	200	V
Gate - Source Voltage	$V_{GS}$	$\pm 20$ $\pm 30$	V
Max. Continuous Drain Current (package limited) @ 25°C	$I_{D1}$	15	A
Max. Instantaneous Drain Current ( $T_J$ limited) $T_C = 25^\circ C$	$I_{D2}$	16	A
Max. Avalanche current	$I_{AS}$	15	A
Single Pulse Avalanche Energy	$E_{AS}$	450	mJ
Total Power Dissipation	$P_D$	63 48	W
Operating & Storage Temperature	$T_{OP} \ \& \ T_{STG}$	-55 to +150	°C
Maximum Thermal Resistance (Junction to Case)	$R_{\theta JC}$	2	°C/W

**NOTES:**

\*Pulse Test: Pulse Width = 300 $\mu$ sec, Duty Cycle = 2%.

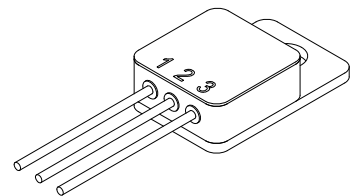
1/ For ordering information, price, and availability - contact factory.

2/ Screening based on MIL-PRF-19500. Screening flows available on request.

3/ Maximum current limited by package configuration

4/ Unless otherwise specified, all electrical characteristics @ 25°C.

**TO-257**





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Electrical Characteristics <sup>4/</sup>		Symbol	Min	Typ	Max	Units
<b>Drain to Source Breakdown Voltage</b>	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	$BV_{DSS}$	200	220	—	V
<b>Drain to Source On State Resistance</b>	$V_{GS} = 10\text{ V}, I_D = 11\text{ A}, T_J = 25^\circ\text{C}$	$R_{DS(on)}$	—	0.13	0.18	$\Omega$
	$V_{GS} = 10\text{ V}, I_D = 11\text{ A}, T_J = 125^\circ\text{C}$		—	0.25	0.48	
	$V_{GS} = 10\text{ V}, I_D = 18\text{ A}, T_J = 25^\circ\text{C}$		—	0.135	0.25	
<b>On State Drain Current</b>	$V_{DS} > I_{D(on)} \times R_{DS(on)} \text{ Max}, V_{GS} = 10\text{ V}, T_J = 25^\circ\text{C}$	$I_{D(on)}$	15	—	—	A
<b>Gate Threshold Voltage</b>	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}, T_J = 25^\circ\text{C}$	$V_{GS(th)}$	2.0	3.0	4.0	V
	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}, T_J = 125^\circ\text{C}$		1.0	2.2	—	
	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}, T_J = -55^\circ\text{C}$		—	3.5	—	
<b>Forward Transconductance</b>	$V_{DS} \geq 10\text{ V}, I_{DS} = 10\text{ A}, T_J = 25^\circ\text{C}$	$g_{fs}$	6.5	10	—	S ( $\Omega$ )
<b>Zero Gate Voltage Drain Current</b>	$V_{DS} = \text{max rated voltage}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	$I_{DSS}$	—	0.02	25	$\mu\text{A}$
	$V_{DS} = \text{max rated voltage}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$		—	10	250	
<b>Gate to Source Leakage Forward Gate to Source Leakage Reverse</b>	At rated $V_{GS}, T_J = 25^\circ\text{C}$	$I_{GSS1}$	—	10	100	nA
			—	10	-100	
	At rated $V_{GS}, T_J = 125^\circ\text{C}$	$I_{GSS2}$	—	10	200	
			—	10	-200	
<b>Total Gate Charge</b>	$V_{GS} = 10\text{ V}$	$Q_g$	—	50	60	nC
<b>Gate to Source Charge</b>	$V_{DS} = 100\text{ V}$	$Q_{gs}$	—	12	15	
<b>Gate to Drain Charge</b>	Rated $I_D$	$Q_{gd}$	—	30	38	
<b>Turn on Delay Time</b>	$V_{DD} = 100\text{ V}$	$t_{d(on)}$	—	20	30	nsec
<b>Rise Time</b>	$I_D = 11\text{ A}$	$t_r$	—	40	90	
<b>Turn off Delay Time</b>	$R_G = 9.1\ \Omega$	$t_{d(off)}$	—	55	75	
<b>Fall Time</b>	$V_{GS} = 10\text{ V}$	$t_f$	—	30	50	
<b>Diode Forward Voltage</b>	$I_S = \text{Rated } I_D, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	$V_{SD}$	—	—	1.5	V
<b>Diode Reverse Recovery Time</b>	$T_J = 25^\circ\text{C}, I_F = \text{Rated } I_D, di/dt = 100\text{ A}/\mu\text{sec}$	$t_{rr}$	—	290	500	nsec
<b>Reverse Recovery Charge</b>		$Q_{rr}$	—	2.6	5.3	$\mu\text{C}$
<b>Input Capacitance</b>	$V_{GS} = 0\text{ V}$	$C_{iss}$	—	1200	—	pF
<b>Output Capacitance</b>	$V_{DS} = 25\text{ V}$	$C_{oss}$	—	450	—	
<b>Reverse Transfer Capacitance</b>	$f = 1\text{ MHz}$	$C_{rss}$	—	150	—	

**NOTE:** All specifications are subject to change without notification.  
 SCD's for these devices should be reviewed by SSDI prior to release.

**DATA SHEET #: F00111C**

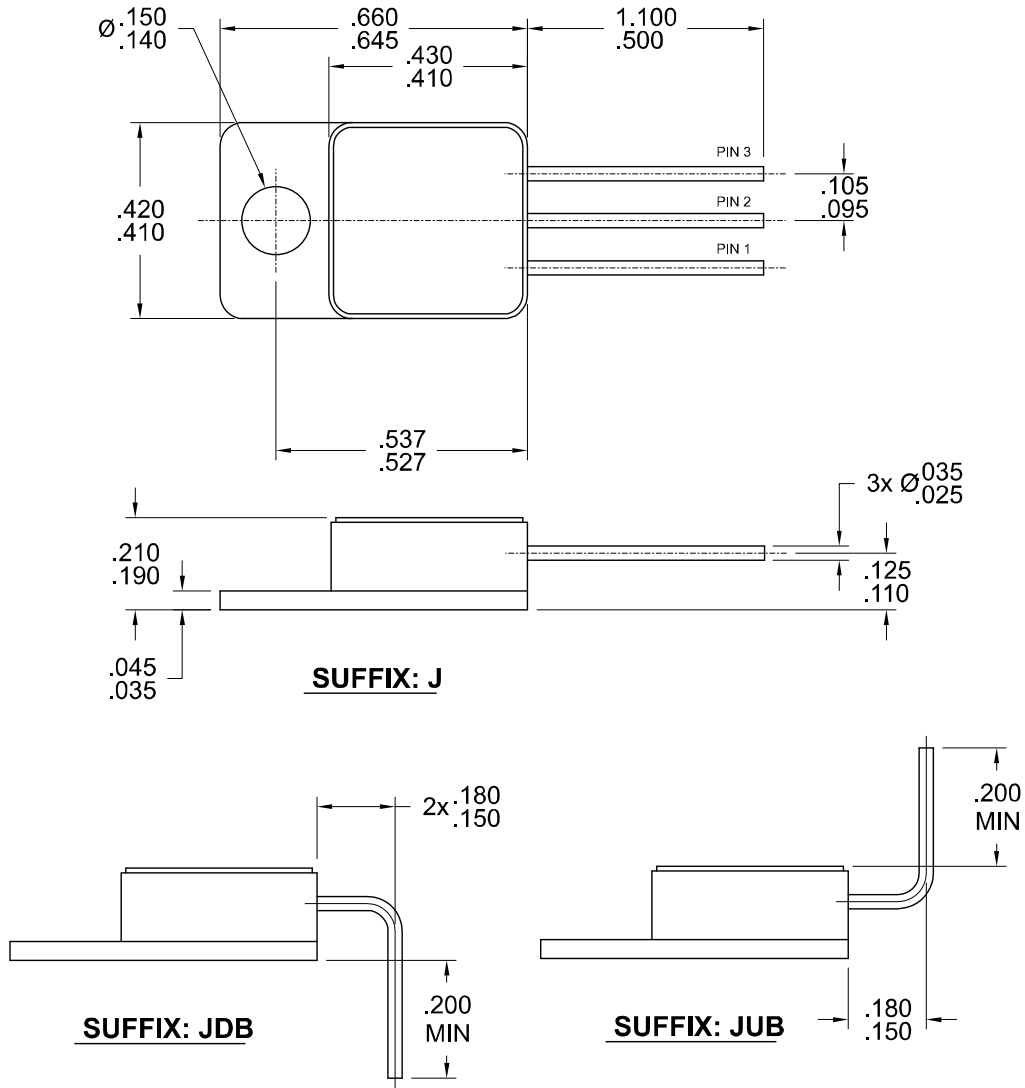
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# SFF240J SFF240JR

### TO-257 (J)



#### PIN ASSIGNMENT (Standard)

Package	Pin 1	Pin 2	Pin 3
TO-257 (J)	Drain	Source	Gate
TO-257 (JR)	Gate	Drain	Source

#### Available Part Numbers:

SFF240J, SFF240JR, SFF240JUB, SFF240JUBR, SFF240JDB, SFF240JDBR

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